

Automotive P-Channel 30 V (D-S) 175 °C MOSFET

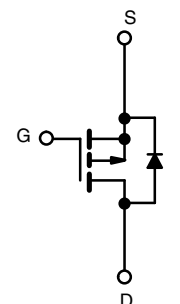
PowerPAK® SO-8L Single


FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_g and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE



P-Channel MOSFET

PRODUCT SUMMARY

V_{DS} (V)	-30
$R_{DS(on)}$ (Ω) at $V_{GS} = -10$ V	0.0044
$R_{DS(on)}$ (Ω) at $V_{GS} = -4.5$ V	0.0071
I_D (A)	-60
Configuration	Single
Package	PowerPAK SO-8L

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	V_{DS}	-30	V
Gate-source voltage	V_{GS}	± 20	
Continuous drain current	I_D	$T_C = 25$ °C ^a	A
		$T_C = 125$ °C	
Continuous source current (diode conduction) ^a	I_S	-60	
Pulsed drain current ^b	I_{DM}	-155	
Single pulse avalanche current	I_{AS}	-41	
Single pulse avalanche energy	E_{AS}	84	mJ
Maximum power dissipation ^b	P_D	$T_C = 25$ °C	W
		$T_C = 125$ °C	
Operating junction and storage temperature range	T_J, T_{stg}	-55 to +175	°C
Soldering recommendations (peak temperature) ^{d, e}		260	

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-ambient	R_{thJA}	68	°C/W
Junction-to-case (drain)	R_{thJC}	2.2	

Notes

- Package limited.
- Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %.
- When mounted on 1" square PCB (FR4 material).
- See solder profile (www.vishay.com/doc?73257). For PowerPAK SO-8L, the end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.



SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0, I _D = -250 μA		-30	-	-	V
Gate-source threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250 μA		-1.5	-2.0	-2.5	
Gate-source leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V		-	-	± 100	nA
Zero gate voltage drain current	I _{DSS}	V _{GS} = 0 V	V _{DS} = -30 V	-	-	-1	μA
		V _{GS} = 0 V	V _{DS} = -30 V, T _J = 125 °C	-	-	-50	
		V _{GS} = 0 V	V _{DS} = -30 V, T _J = 175 °C	-	-	-200	
On-state drain current ^a	I _{D(on)}	V _{GS} = -10 V	V _{DS} ≥ -5 V	-30	-	-	A
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = -10 V	I _D = -10 A	-	0.0036	0.0044	Ω
		V _{GS} = -10 V	I _D = -10 A, T _J = 125 °C	-	-	0.0060	
		V _{GS} = -10 V	I _D = -10 A, T _J = 175 °C	-	-	0.0068	
		V _{GS} = -4.5 V	I _D = -6 A	-	0.0059	0.0071	
Forward transconductance ^b	g _{fs}	V _{DS} = -15 V, I _D = -10 A		-	60	-	S
Dynamic ^b							
Input capacitance	C _{iss}	V _{GS} = 0 V	V _{DS} = -25 V, f = 1 MHz	-	8200	10 700	pF
Output capacitance	C _{oss}			-	950	1300	
Reverse transfer capacitance	C _{rss}			-	785	1050	
Total gate charge ^c	Q _g	V _{GS} = -10 V	V _{DS} = -15 V, I _D = -5 A	-	169	260	nC
Gate-source charge ^c	Q _{gs}			-	24	-	
Gate-drain charge ^c	Q _{gd}			-	32	-	
Gate resistance	R _g	f = 1 MHz		0.5	1.05	1.6	Ω
Turn-on delay time ^c	t _{d(on)}	V _{DD} = -15 V, R _L = 3 Ω I _D ≅ -5 A, V _{GEN} = -10 V, R _g = 1 Ω		-	23	35	ns
Rise time ^c	t _r			-	19	30	
Turn-off delay time ^c	t _{d(off)}			-	72	120	
Fall time ^c	t _f			-	14	25	
Source-Drain Diode Ratings and Characteristics ^b							
Pulsed current ^a	I _{SM}			-	-	-155	A
Forward voltage	V _{SD}	I _F = -10 A, V _{GS} = 0 V		-	-0.75	-1.2	V
Body diode reverse recovery time	t _{rr}	I _F = 10 A, di/dt = 100 A/μs		-	39	90	ns
Body diode reverse recovery charge	Q _{rr}			-	45	100	nC
Reverse recovery fall time	t _a			-	22	-	ns
Reverse recovery rise time	t _b			-	19	-	
Body diode peak reverse recovery current	I _{RM(REC)}			-	-2.3	-	A

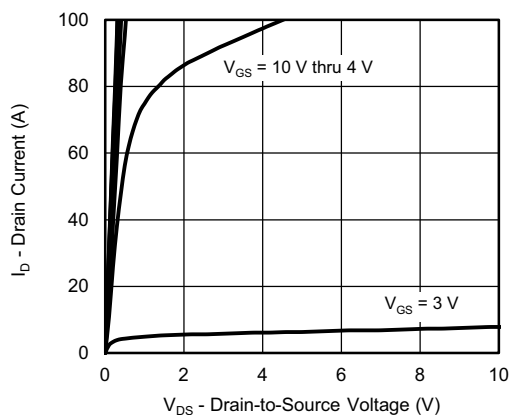
Notes

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

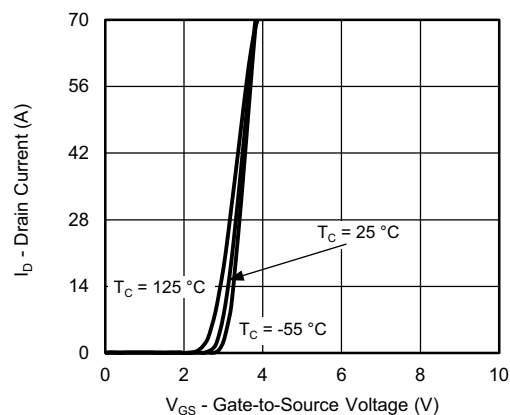
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



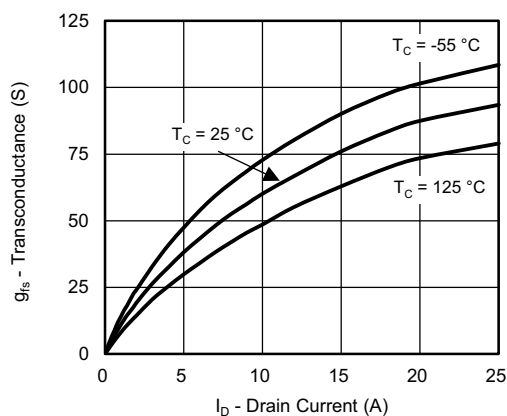
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



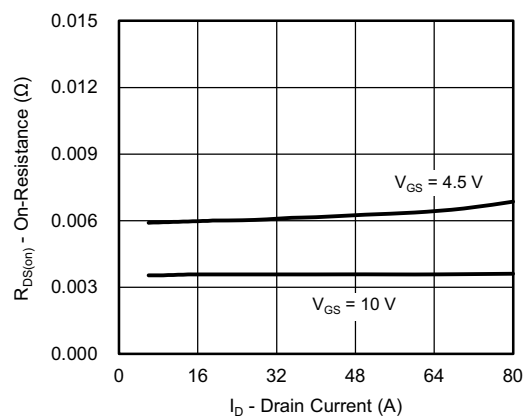
Output Characteristics



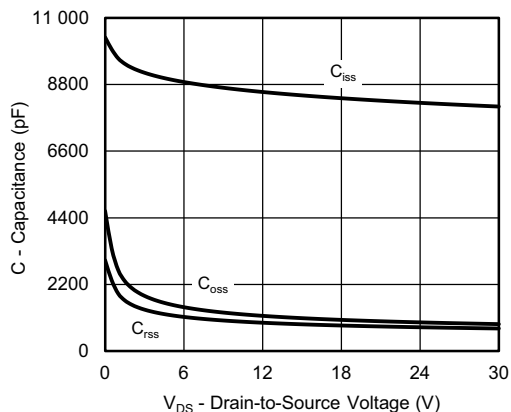
Transfer Characteristics



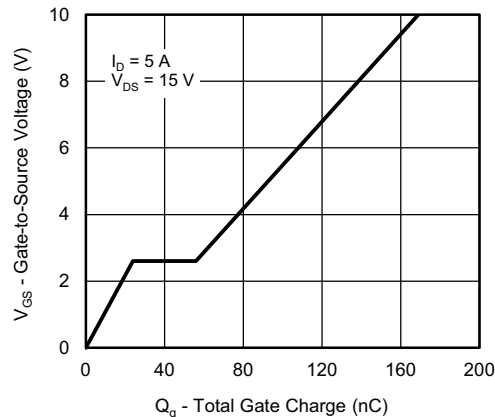
Transconductance



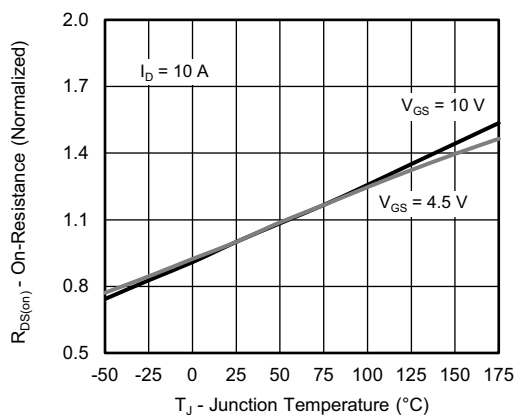
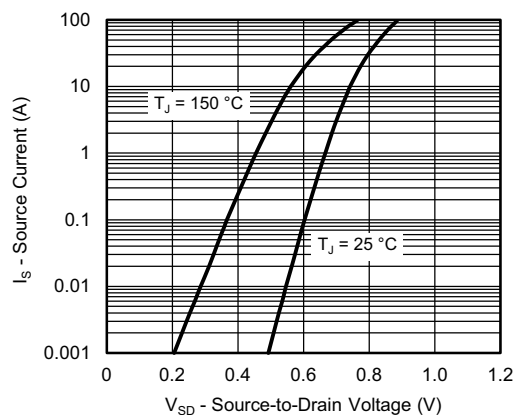
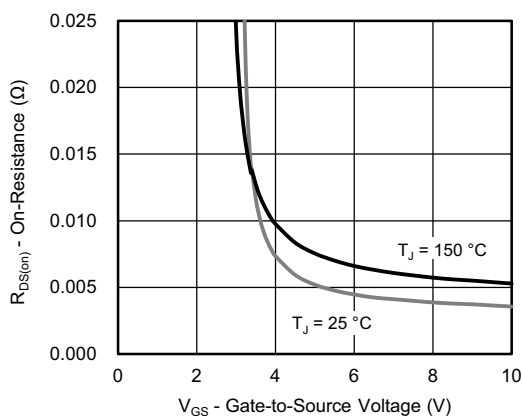
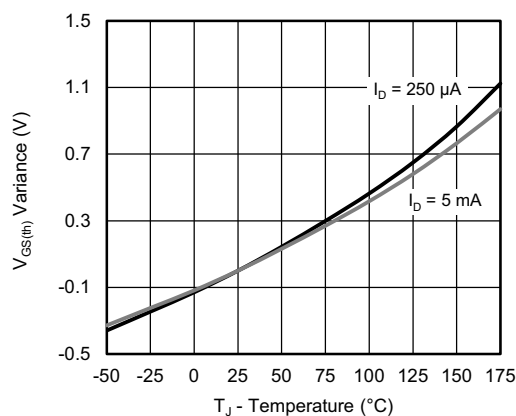
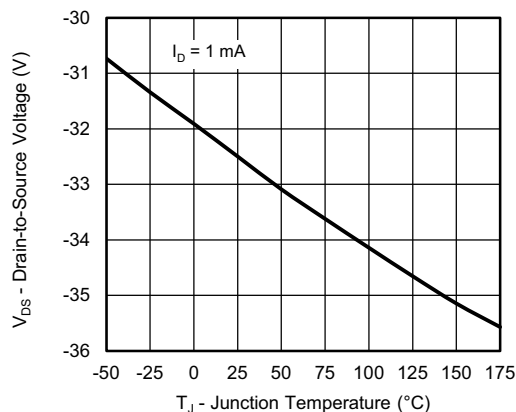
On-Resistance vs. Drain Current



Capacitance

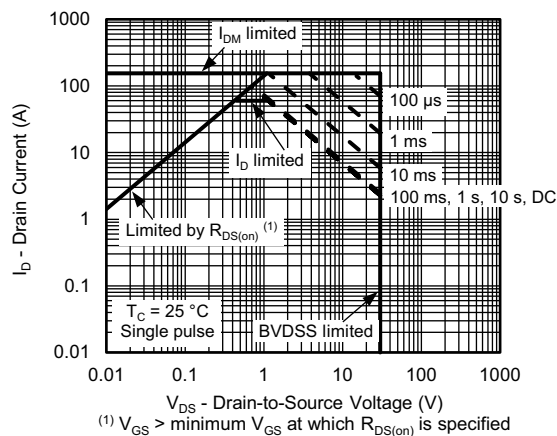


Gate Charge

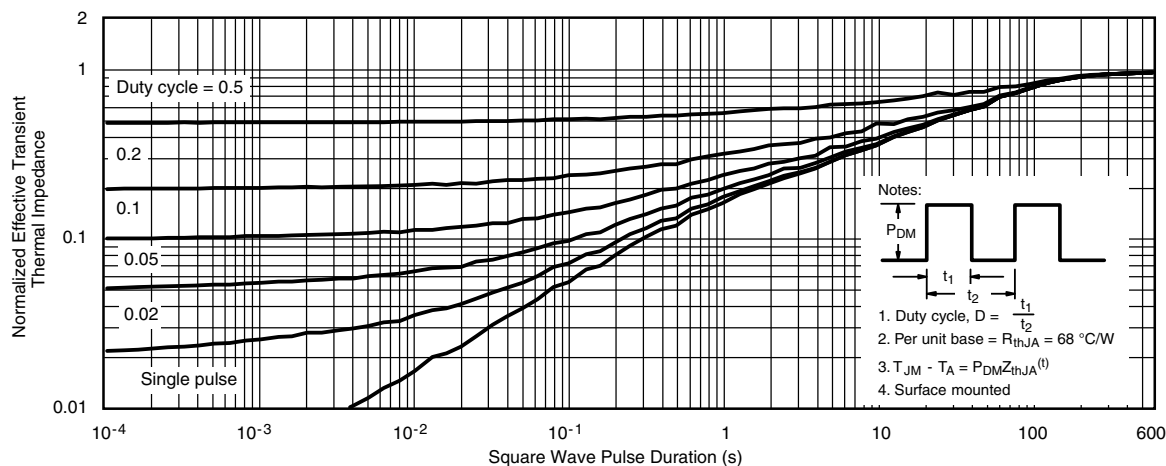
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

On-Resistance vs. Junction Temperature

Source Drain Diode Forward Voltage

On-Resistance vs. Gate-to-Source Voltage

Threshold Voltage

Drain-Source Breakdown vs. Junction Temperature



THERMAL RATINGS ($T_C = 25\text{ }^\circ\text{C}$, unless otherwise noted)



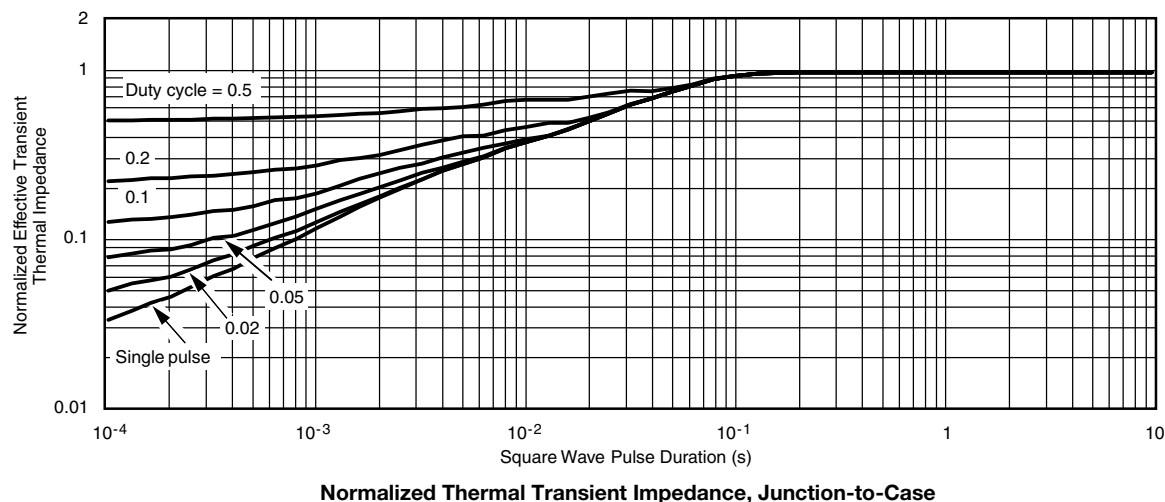
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS ($T_C = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient ($25\text{ }^{\circ}\text{C}$)
 - Normalized Transient Thermal Impedance Junction-to-Case ($25\text{ }^{\circ}\text{C}$)are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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